

Vishay Semiconductors

AUTOMOTIVE GRADE

> COMPLIANT HALOGEN

FREE

Ultrafast Rectifier, 1 A FRED Pt®





MicroSMP (DO-219AD)

Anode O Cathode

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{F(AV)}	1 A			
V_{R}	100 V, 200 V			
V _F at I _F	at I _F 0.72 V			
t _{rr} (typ.)	33 ns			
I _{FSM}	30 A			
T _J max.	175 °C			
Package	MicroSMP (DO-219AD)			
Circuit configuration	Single			

FEATURES

- Very low profile typical height of 0.65 mm
- · Ideal for automated placement
- Low forward voltage drop, low power losses
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

MECHANICAL DATA

Case: MicroSMP (DO-219AD)

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

J-STD-002, meets JESD 201 class 2 whisker test

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
VS-1EQH01HM		.,		100	V	
Peak repetitive reverse voltage	VS-1EQH02HM3	V_{RRM}		200	Į v	
Average rectified forward current		I _{F(AV)}	T _M = 159 °C	1	۸	
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C, 10 ms sine pulse	30	Α	
Operating junction and storage temperatures		T _J , T _{Stg}		-55 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage,	VS-1EQH01HM3	V _{BR} ,	1. 100	100	-	-	- V
blocking voltage	VS-1EQH02HM3	V_R	I _R = 100 μA	200			
Enward voltage		V _F	I _F = 1 A	-	0.88	0.97	
Forward voltage		٧F	I _F = 1 A, T _J = 150 °C	-	0.72	0.75	
Reverse leakage current		I _R	V _R = V _R rated	-	-	1	μA
			$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	25	
Junction capacitance		C _T	V _R = 200 V	-	6	-	pF

Revision: 08-Nov-2021 **1** Document Number: 96563 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u>

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS		TYP.	MAX.	UNITS
Reverse recovery time	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt =$	$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		33	-	
		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}$	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	23	1
		T _J = 25 °C		-	13	-	ns
		T _J = 125 °C		-	18	-	
Dools was a very a commant	I _{RRM}	$T_J = 25 ^{\circ}\text{C}$ $I_F = 1 \text{A}$	-	1.8	-	^	
Peak recovery current		I_{RRM} $T_{J} = 125 ^{\circ}C$ $T_{R} = 100 V$ $T_{R} = 100 V$	-	2.7	-	Α	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	11	-	nC
		T _J = 125 °C		-	23	-	110

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to mount		R _{thJM} ⁽¹⁾		-	16	20	
Thermal resistance, junction to ambient		R _{thJA}	Device mounted on FR4 PCB, 2 oz. standard footprint	-	160	-	°C/W
Marking device VS-1EQH01HM3 VS-1EQH02HM3			Case style MicroSMP (DO-219AD)	1H1		•	
			Case style MicrosMP (DO-219AD)	1H2			

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

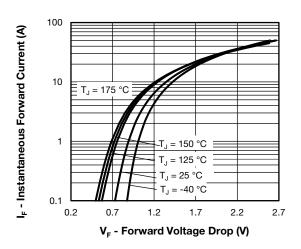


Fig. 1 - Typical Forward Voltage Drop Characteristics

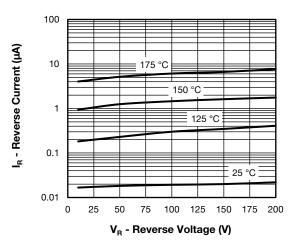


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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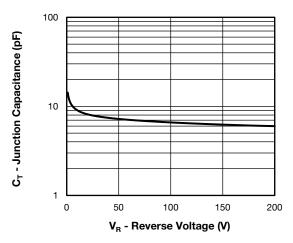


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

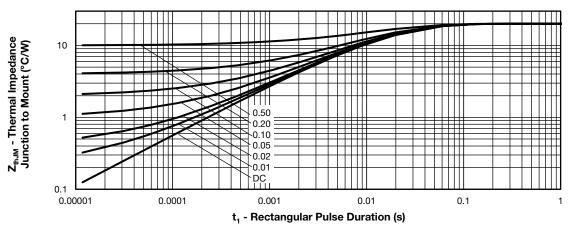


Fig. 4 - Maximum Transient Thermal Impedance, Junction to Mount

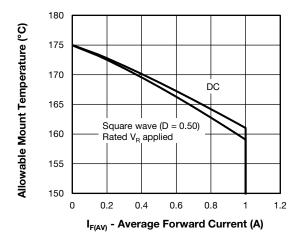


Fig. 5 - Maximum Allowable Mount Temperature vs. Average Forward Current

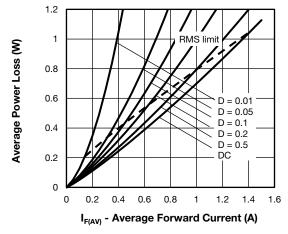


Fig. 6 - Forward Power Loss Characteristics

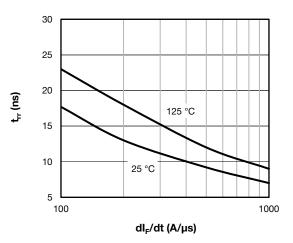
Note

Formula used: $T_M = T_J$ - (Pd + Pd_{REV}) x R_{thJM}; Pd = forward power loss = $I_{F(AV)}$ x V_{FM} at ($I_{F(AV)}$ /D) (see fig. 5); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R

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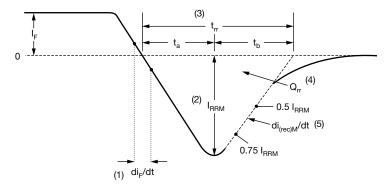


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35 30 125 °C 25 Q_{rr} (nC) 20 25 °C 15 10 5 100 1000 dl_F/dt (A/μs)

Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $t_{\rm pr}$ reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

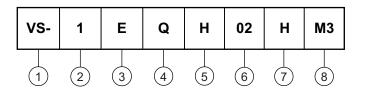
Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (1 = 1 A)

Circuit configuration:

E = single diode

4 - Q = MicroSMP package

5 - Process type,

H = ultrafast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	PREFERRED PACKAGE CODE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION					
VS-1EQH01HM3/H	Н	4500	7" diameter plastic tape and reel			
VS-1EQH02HM3/H	Н	4500	7" diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96591</u>				
Part marking information	www.vishay.com/doc?96590			
Packaging information	www.vishay.com/doc?88869			
SPICE model	www.vishay.com/doc?96594			

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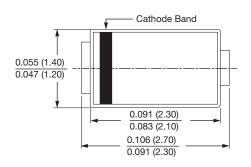


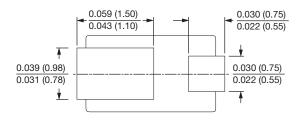


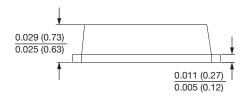
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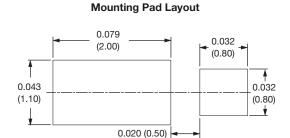
MicroSMP (DO-219AD), FRED Pt®

DIMENSIONS in inches (millimeters)









Legal Disclaimer Notice



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